Rochester Electronics

Datasheet

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
    - Class Q Military
    - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)

    - Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

National Semiconductor

May 1995

54F/74F373
Octal Transparent Latch with TRI-STATE® Outputs

General Description

The 'F373 consists of eight latches with TRI-STATE outputs for bus organized system applications. The flip-flops appear transparent to the data when Latch Enable (LE) is HIGH. When LE is LOW, the data that meets the setup times is latched. Data appears on the bus when the Output Enable ($\overline{OE}$) is LOW. When $\overline{OE}$ is HIGH the bus output is in the high impedance state.

Features

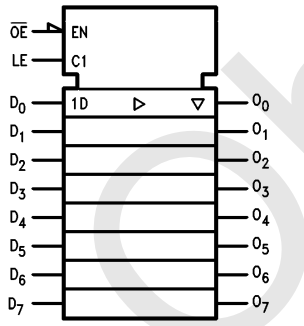
- Eight latches in a single package
- TRI-STATE outputs for bus interfacing
- Guaranteed 4000V minimum ESD protection

Commercial	Military	Package Number	Package Description
74F373PC		N20A	20-Lead (0.300″ Wide) Molded Dual-In-Line
	54F373DM (QB)	J20A	20-Lead Ceramic Dual-In-Line
74F373SC (Note 1)		M20B	20-Lead (0.300″ Wide) Molded Small Outline, JEDEC
74F373SJ (Note 1)		M20D	20-Lead (0.300″ Wide) Molded Small Outline, EIAJ
74F373MSA (Note 1)		MSA20	20-Lead Molded Shrink Small Outline, EIAJ Type II
	54F373FM (QB)	W20A	20-Lead Cerpack
	54F373LM (QB)	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C

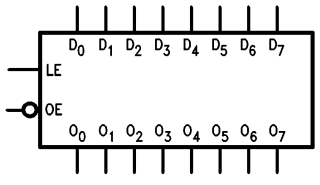
Note 1: Devices also available in 13″ reel. Use suffix = SCX, SJX, and MSAX.

Logic Symbols

IEEE/IEC



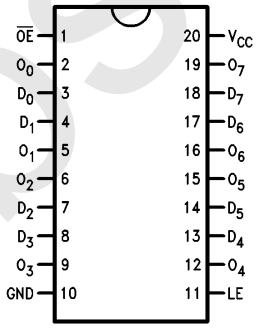
TL/F/9523–4



TL/F/9523–1

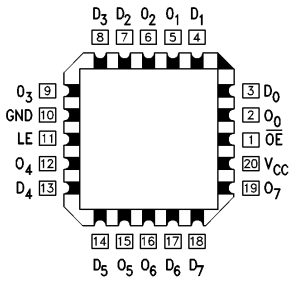
Connection Diagrams

Pin Assignment for DIP, SOIC, SSOP and Flatpak



TL/F/9523–2

Pin Assignment for LCC



TL/F/9523–3

TRI-STATE® is a registered trademark of National Semiconductor Corporation.

RRD-B30M75/Printed in U. S. A.

Unit Loading/Fan Out

Pin Names	Description	54F/74F	
		U.L. HIGH/LOW	Input I_{IH}/I_{IL} Output I_{OH}/I_{OL}
D_0–D_7	Data Inputs	1.0/1.0	20 μA/ −0.6 mA
LE	Latch Enable Input (Active HIGH)	1.0/1.0	20 μA/ −0.6 mA
$\overline{OE}$	Output Enable Input (Active LOW)	1.0/1.0	20 μA/ −0.6 mA
O_0–O_7	TRI-STATE Latch Outputs	150/40 (33.3)	−3 mA/24 mA (20 mA)

Functional Description

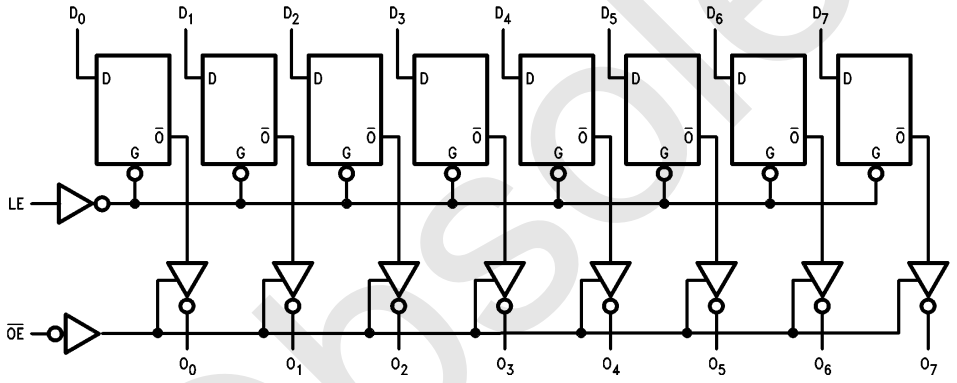
The ’F373 contains eight D-type latches with TRI-STATE output buffers. When the Latch Enable (LE) input is HIGH, data on the D_n inputs enters the latches. In this condition the latches are transparent, i.e., a latch output will change state each time its D input changes. When LE is LOW, the latches store the information that was present on the D inputs a setup time preceding the HIGH-to-LOW transition of LE. The TRI-STATE buffers are controlled by the Output Enable ($\overline{OE}$) input. When $\overline{OE}$ is LOW, the buffers are in the bi-state mode. When $\overline{OE}$ is HIGH the buffers are in the high impedance mode but this does not interfere with entering new data into the latches.

Truth Table

Inputs			Output
LE	$\overline{OE}$	D_n	O_n
H	L	H	H
H	L	L	L
L	L	X	O_n (no change)
X	H	X	Z

H = HIGH Voltage Level
L = LOW Voltage Level
X = Immaterial
Z = High Impedance State

Logic Diagram



TL/F/9523–5

Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature	−65°C to +150°C
Ambient Temperature under Bias	−55°C to +125°C
Junction Temperature under Bias	−55°C to +175°C
Plastic	−55°C to +150°C
V_{CC} Pin Potential to Ground Pin	−0.5V to +7.0V
Input Voltage (Note 2)	−0.5V to +7.0V
Input Current (Note 2)	−30 mA to +5.0 mA
Voltage Applied to Output in HIGH State (with V_{CC} = 0V)	
Standard Output	−0.5V to V_{CC}
TRI-STATE Output	−0.5V to +5.5V
Current Applied to Output in LOW State (Max)	twice the rated I_{OL} (mA)
ESD Last Passing Voltage (Min)	4000V

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

Recommended Operating Conditions

Free Air Ambient Temperature	
Military	−55°C to +125°C
Commercial	0°C to +70°C
Supply Voltage	
Military	+4.5V to +5.5V
Commercial	+4.5V to +5.5V

DC Electrical Characteristics

Symbol	Parameter		54F/74F Min	54F/74F Typ	54F/74F Max	Units	V_{CC}	Conditions
V_{IH}	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signal
V_{IL}	Input LOW Voltage				0.8	V		Recognized as a LOW Signal
V_{CD}	Input Clamp Diode Voltage				−1.2	V	Min	I_{IN} = −18 mA
V_{OH}	Output HIGH Voltage	54F 10% V_{CC}	2.5			V	Min	I_{OH} = −1 mA
		54F 10% V_{CC}	2.4					I_{OH} = −3 mA
		74F 10% V_{CC}	2.5					I_{OH} = −1 mA
		74F 10% V_{CC}	2.4					I_{OH} = −3 mA
		74F 5% V_{CC}	2.7					I_{OH} = −1 mA
		74F 5% V_{CC}	2.7					I_{OH} = −3 mA
V_{OL}	Output LOW Voltage	54F 10% V_{CC}			0.5	V	Min	I_{OL} = 20 mA
		74F 10% V_{CC}			0.5			I_{OL} = 24 mA
I_{IH}	Input HIGH Current	54F			20.0	μA	Max	V_{IN} = 2.7V
		74F			5.0			
I_{BVI}	Input HIGH Current Breakdown Test	54F			100	μA	Max	V_{IN} = 7.0V
		74F			7.0			
I_{CEX}	Output HIGH Leakage Current	54F			250	μA	Max	V_{OUT} = V_{CC}
		74F			50			
V_{ID}	Input Leakage Test	74F	4.75			V	0.0	I_{ID} = 1.9 μA All Other Pins Grounded
I_{OD}	Output Leakage Circuit Current	74F			3.75	μA	0.0	V_{IOD} = 150 mV All Other Pins Grounded
I_{IL}	Input LOW Current				−0.6	mA	Max	V_{IN} = 0.5V
I_{OZH}	Output Leakage Current				50	μA	Max	V_{OUT} = 2.7V
I_{OZL}	Output Leakage Current				−50	μA	Max	V_{OUT} = 0.5V
I_{OS}	Output Short-Circuit Current		−60		−150	mA	Max	V_{OUT} = 0V
I_{ZZ}	Bus Drainage Test				500	μA	0.0V	V_{OUT} = 5.25V
I_{CCZ}	Power Supply Current			38	55	mA	Max	V_O = HIGH Z

AC Electrical Characteristics

Symbol	Parameter	74F $T_A = +25°C$, $V_{CC} = +5.0V$, $C_L = 50$ pF			54F $T_A, V_{CC} =$ Mil, $C_L = 50$ pF		74F $T_A, V_{CC} =$ Com, $C_L = 50$ pF		Units
		Min	Typ	Max	Min	Max	Min	Max	
t_{PLH} t_{PHL}	Propagation Delay D_n to O_n	3.0 2.0	5.3 3.7	7.0 5.0	3.0 2.0	8.5 7.0	3.0 2.0	8.0 6.0	ns
t_{PLH} t_{PHL}	Propagation Delay LE to O_n	5.0 3.0	9.0 5.2	11.5 7.0	5.0 3.0	15.0 8.5	5.0 3.0	13.0 8.0	ns
t_{PZH} t_{PZL}	Output Enable Time	2.0 2.0	5.0 5.6	11.0 7.5	2.0 2.0	13.5 10.0	2.0 2.0	12.0 8.5	ns
t_{PHZ} t_{PLZ}	Output Disable Time	1.5 1.5	4.5 3.8	6.5 5.0	1.5 1.5	10.0 7.0	1.5 1.5	7.5 6.0	ns

AC Operating Requirements

Symbol	Parameter	74F $T_A = +25°C$, $V_{CC} = +5.0V$		54F $T_A, V_{CC} =$ Mil		74F $T_A, V_{CC} =$ Com		Units
		Min	Max	Min	Max	Min	Max	
$t_s(H)$ $t_s(L)$	Setup Time, HIGH or LOW D_n to LE	2.0 2.0		2.0 2.0		2.0 2.0		ns
$t_h(H)$ $t_h(L)$	Hold Time, HIGH or LOW D_n to LE	3.0 3.0		3.0 4.0		3.0 3.0		ns
$t_w(H)$	LE Pulse Width, HIGH	6.0		6.0		6.0		ns

Ordering Information

The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:

74F 373 S C X

Temperature Range Family
74F = Commercial
54F = Military

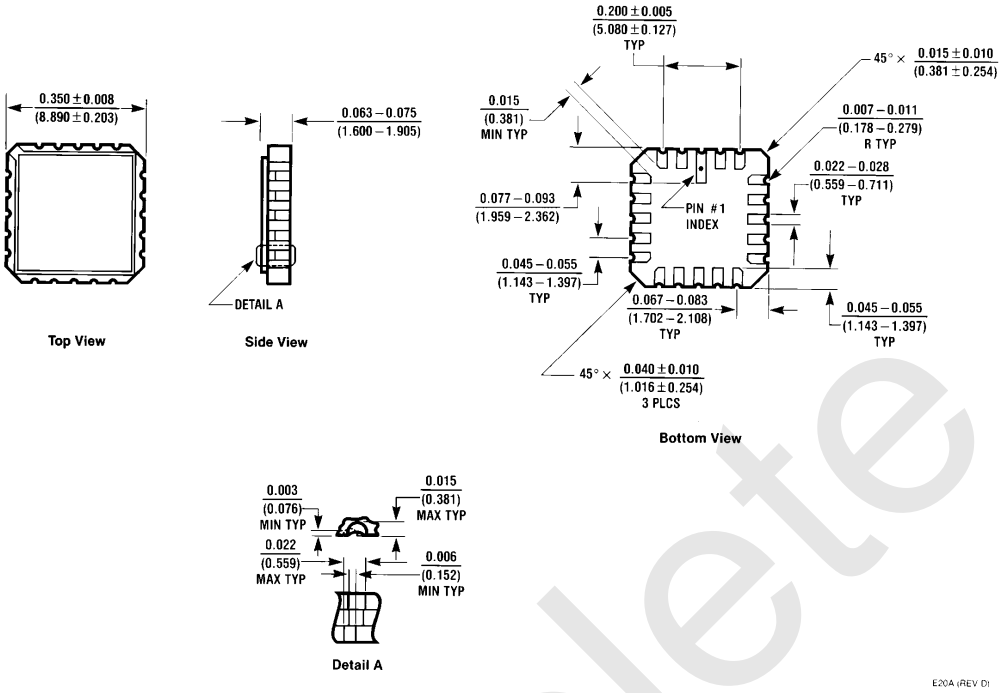
Device Type

Package Code
P = Plastic DIP
D = Ceramic DIP
F = Flatpak
L = Leadless Chip Carrier (LCC)
S = Small Outline SOIC JEDEC
SJ = Small Outline SOIC EIAJ
MSA = Shrink Small Outline (EIAJ SSOP)

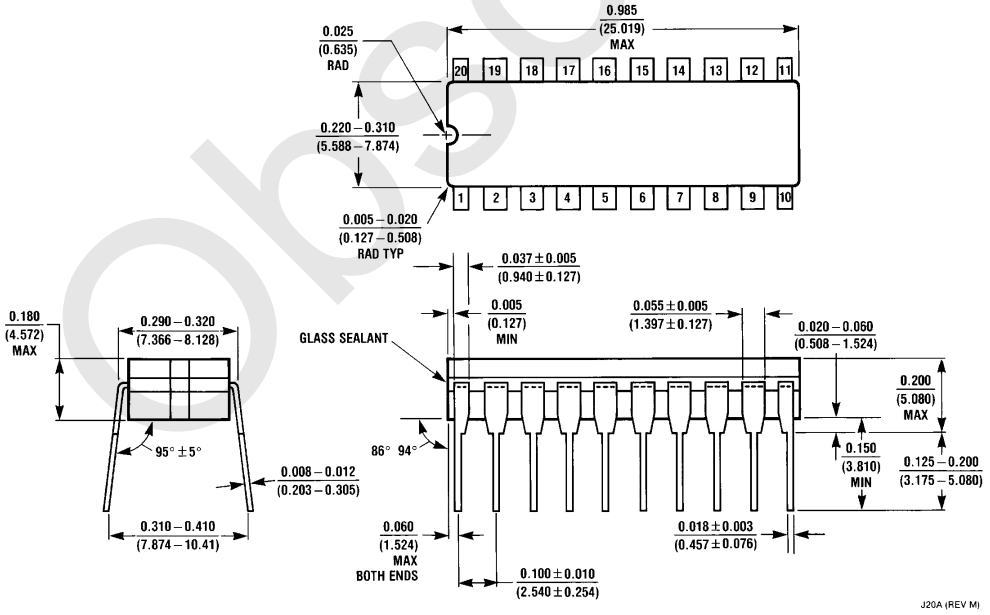
Special Variations
QB = Military grade device with environmental and burn-in processing
X = Devices shipped in 13″ reel

Temperature Range
C = Commercial (0°C to +70°C)
M = Military (−55°C to +125°C)
NOTE:
Not required for MSA package code

Physical Dimensions inches (millimeters)

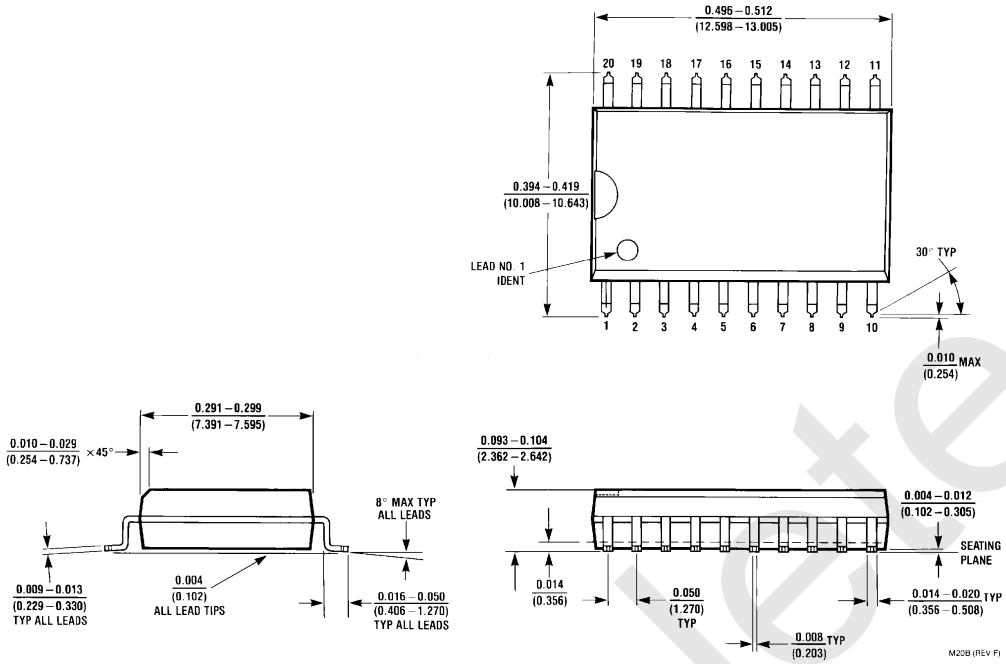


20-Lead Ceramic Leadless Chip Carrier (L)
NS Package Number E20A

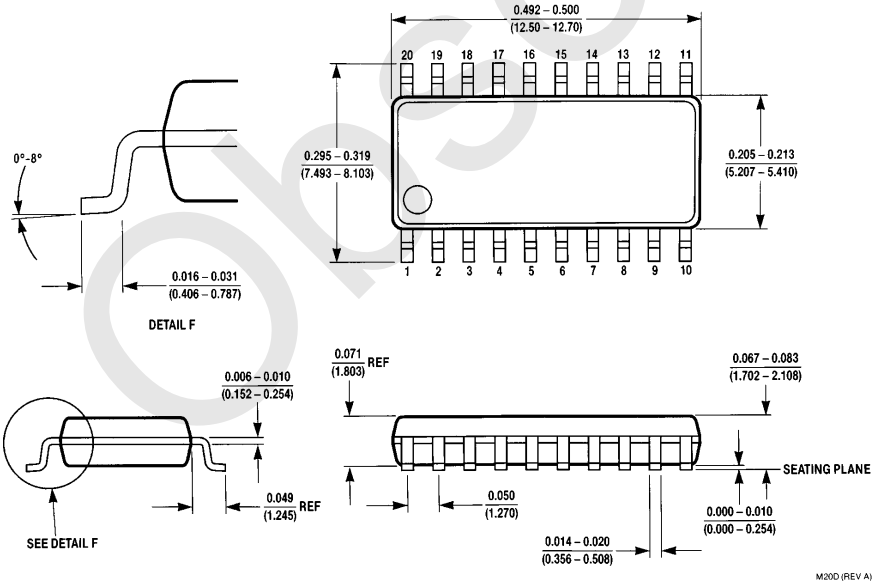


20-Lead Ceramic Dual-In-Line Package (D)
NS Package Number J20A

Physical Dimensions inches (millimeters) (Continued)

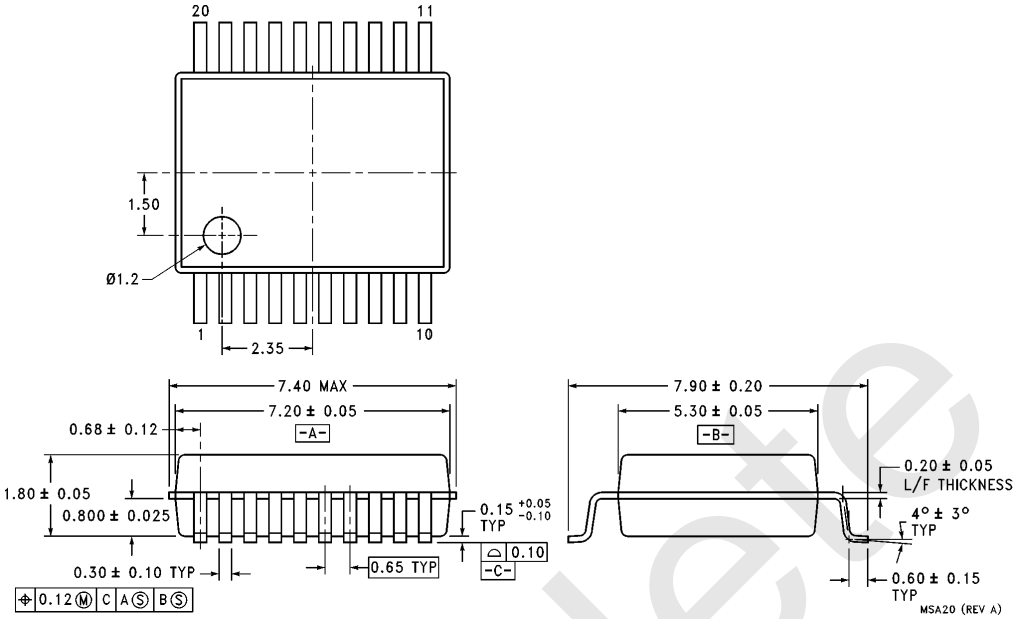


20-Lead (0.300″ Wide) Molded Small Outline Package, JEDEC (S)
NS Package Number M20B

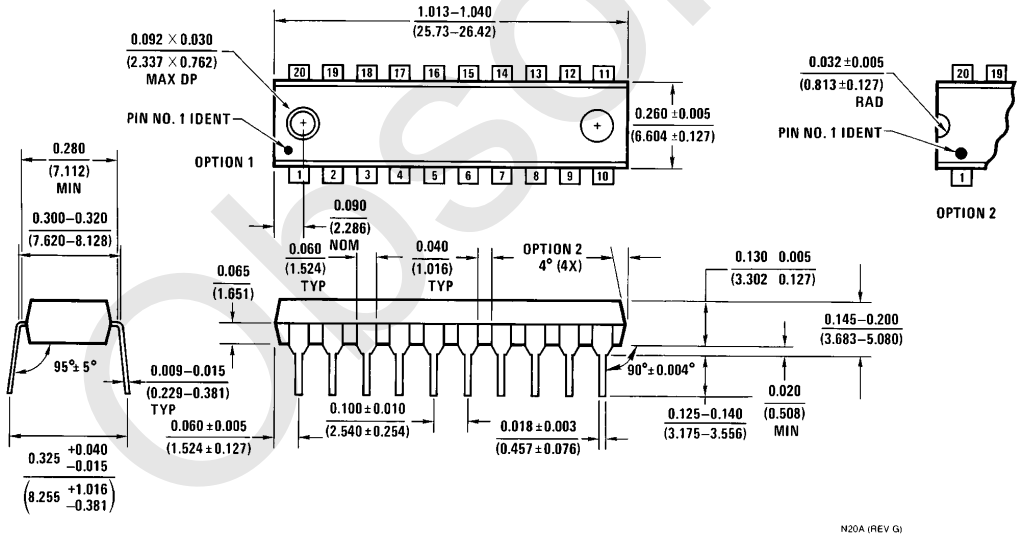


20-Lead (0.300″ Wide) Small Outline Package, EIAJ (SJ)
NS Package Number M20D

Physical Dimensions inches (millimeters) (Continued)

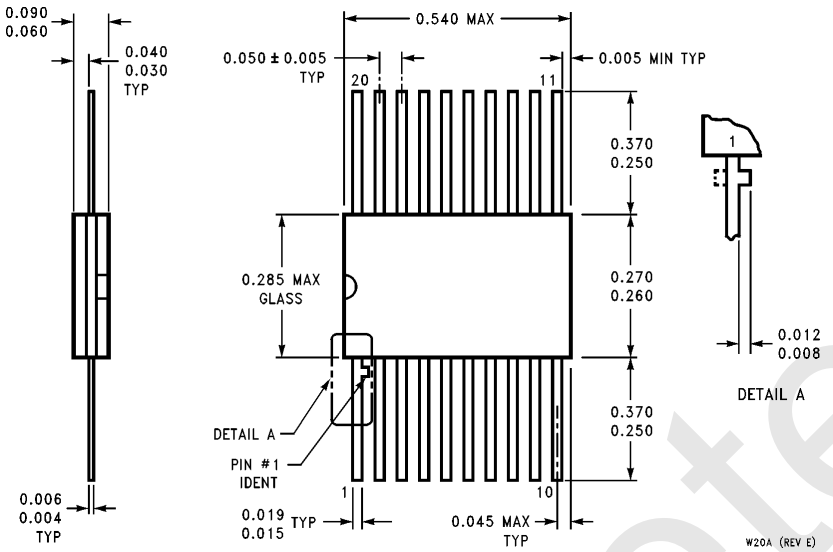


20-Lead Molded Shrink Small Outline Package, EIAJ, Type II (MSA)
NS Package Number MSA20



20-Lead (0.300″ Wide) Molded Dual-In-Line Package (P)
NS Package Number N20A

Physical Dimensions inches (millimeters) (Continued)



20-Lead Ceramic Flatpak (F)
NS Package Number W20A

LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

National Semiconductor Corporation
2900 Semiconductor Drive
P.O. Box 58090
Santa Clara, CA 95052-8090
Tel: 1(800) 272-9959
TWX: (910) 339-9240

National Semiconductor GmbH
Livry-Gargan-Str. 10
D-82256 Fürstenfeldbruck
Germany
Tel: (81-41) 35-0
Telex: 527649
Fax: (81-41) 35-1

National Semiconductor Japan Ltd.
Sumitomo Chemical
Engineering Center
Bldg. 7F
1-7-1, Nakase, Mihama-Ku
Chiba-City,
Ciba Prefecture 261
Tel: (043) 299-2300
Fax: (043) 299-2500

National Semiconductor Hong Kong Ltd.
13th Floor, Straight Block,
Ocean Centre, 5 Canton Rd.
Tsimshatsui, Kowloon
Hong Kong
Tel: (852) 2737-1600
Fax: (852) 2736-9960

National Semiconductores Do Brazil Ltda.
Rue Deputado Lacorda Franco
120-3A
Sao Paulo-SP
Brazil 05418-000
Tel: (55-11) 212-5066
Telex: 391-1131931 NSBR BR
Fax: (55-11) 212-1181

National Semiconductor (Australia) Pty, Ltd.
Building 16
Business Park Drive
Monash Business Park
Nottinghill, Melbourne
Victoria 3168 Australia
Tel: (3) 558-9999
Fax: (3) 558-9998